

- 3.7. From the condition  $f_c(E'_2) \geq f_c(E'_1)$  prove the Bernard–Duraffourg relation  $E'_{F_c} - E'_{F_v} \geq \hbar\nu$ .
- 3.8. With the help of Fig. 3.15b calculate for GaAs: The values of  $E_{F_c}$  and  $E_{F_v}$  at  $N = 1.6 \times 10^{18} \text{ cm}^{-3}$  carrier injection and the overall gain bandwidth at the same injection level.
- 3.9. In the energy reference system in Fig. 3.9a calculate for GaAs the energies  $E_2$  and  $E_1$  of the upper and lower laser levels for a transition energy exceeding the band gap energy by  $0.45kT$ .
- 3.10. With the help of Fig. 3.16 for a bulk GaAs semiconductor, calculate the expected gain at a photon energy exceeding the band gap energy by  $0.45kT$  and for a carrier injection of  $N = 1.6 \times 10^{18} \text{ cm}^{-3}$ .

**Example 3.6.** Calculation of the absorption coefficient for GaAs. As an approximation we assume the frequency  $\nu$ , in the first term on the right-hand side of Eq. (3.2.36), to have the value  $\nu \cong E_g/\hbar = 3.43 \times 10^{14} \text{ Hz}$ , where the energy gap  $E_g$  is taken to be 1.424 eV. We also take  $m_c = 0.46m_0$  and  $m_v = 0.067m_0$ , so that  $m_r = 0.059 m_0 = 5.37 \times 10^{-32} \text{ kg}$ . To calculate the average dipole moment  $\mu_{av} = (\mu^2/3)^{1/2}$ , we recall that the accurate value of the average electron momentum  $M_{av}$  was shown to be such that  $M_{av}^2 = 3.38 m_0 E_g$ .<sup>(5)</sup> The relation between average dipole moment and electron momentum is  $M_{av} = m_0 \omega |\mu_{av}|/e$ ,<sup>(5)</sup> so that

$$\mu_{av} = e(3.38E_g/m_0)^{1/2}/2\pi\nu \cong 0.68 \times 10^{-25} \text{ C} \times \text{m}.$$

Note that, if we write  $r_{av} = \mu_{av}/e$ , then  $r_{av} \cong 0.426 \text{ nm}$ . Substitution into Eq. (3.2.36) of the values for  $\nu$  and  $\mu_{av}$  just calculated and  $n = 3.64$  for the refractive index gives  $\alpha_0 = 19,760(\hbar\nu - E_g)^{1/2}$ , where  $\alpha_0$  is expressed in  $\text{cm}^{-1}$  and the energy in eV. The absorption coefficient as calculated from the latter expression is plotted against  $E - E_g$  in Fig. 3.16, where  $E = \hbar\nu$ . Note that, when  $\hbar\nu$  exceeds the energy gap by only 10 meV, the absorption coefficient already reaches a very large value ( $\approx 2,000 \text{ cm}^{-1}$ ).

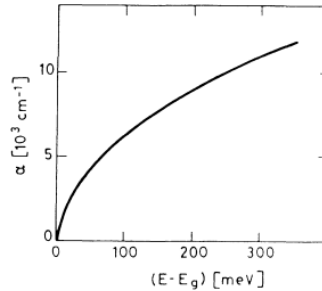


FIG. 3.16. Idealized plot of the absorption coefficient  $\alpha$  versus the difference between the photon energy  $E$  and gap energy  $E_g$  for an intrinsic GaAs bulk semiconductor.

**Example 3.7.** Calculation of the transparency density for GaAs. We first transform Eq. (3.2.40) into the unprimed energy axes in Fig. 3.9a. According to Eq. (3.2.3) we can write  $E'_{F_c} = E_g + E_{F_c}$  and  $E'_{F_v} = -E_{F_v}$ , and Eq. (3.2.40) transforms to  $E_{F_c} + E_{F_v} = 0$ . From Fig. 3.15a we see that  $E_{F_c}/kT$  is a function of  $(N/N_c)$ ; i.e., we can write  $E_{F_c}/kT = f(N/N_c)$ . Similarly we can write  $E_{F_v}/kT = f(N/N_v)$ , so that the transparency condition becomes

$$f(N_r/N_c) + f(N_r/N_v) = 0 \tag{3.2.41}$$

To obtain  $N_r$  from Eq. (3.2.41) for GaAs, we plot the function  $(E_{F_c}/kT) + (E_{F_v}/kT)$  versus  $N$  as a dashed line in Fig. 3.15b. At each carrier concentration  $N$ , the curve is obtained as the sum of values given by the two continuous curves in the figure. According to Eq. (3.2.41), we can now say that the transparency density  $N_r$  is the carrier concentration at which the dashed curve in Fig. 3.15b crosses the zero value of the ordinate. From Fig. 3.15b we obtain  $N_r = 1.2 \times 10^{18} \text{ cm}^{-3}$ .

- 4.4. A Fabry–Perot interferometer consisting of two identical mirrors, air-spaced by a distance  $L$ , is illuminated by a monochromatic em wave of tunable frequency. From a measurement of the transmitted intensity versus the frequency of the input wave we find that the free spectral range of the interferometer is  $3 \times 10^9$  Hz and its resolution is 60 MHz. Calculate the spacing  $L$  of the interferometer, its finesse, and the mirror reflectivity. If the peak transmission is 50% calculate also the mirror loss.
- 4.8. Show that the power contained in a  $TEM_{00}$  Gaussian beam of spot size  $w$  is given by  $P = (\pi w^2/2)I_p$ , where  $I_p$  is the peak ( $r=0$ ) intensity of the beam.
- 4.10. The beam of an Ar laser oscillating in a pure Gaussian  $TEM_{00}$  mode at  $\lambda = 514.5$  nm with an output power of 1 W is sent to a target at a distance of 100 m from the beam waist. If the spot size at the beam waist is  $w_0 = 2$  mm, calculate spot size, radius of curvature of the phase front, and peak intensity at the target position.
- 4.13. A Gaussian beam of waist spot size  $w_0$  is passed through a solid plate of transparent material of length  $L$  and refractive index  $n$ . The plate is placed just in front of the beam waist. Using the  $ABCD$  law of Gaussian beam propagation show that the spot size and radius of curvature of the phase front after the plate are the same as for propagation in a vacuum over a distance  $L' = L/n$ . According to this result, is the far-field divergence angle affected by the insertion of the plate?

**Example 4.3.** *Free-spectral range, finesse, and transmission of a Fabry–Perot etalon.* Consider an FP interferometer made of a piece of glass with two plane parallel surfaces coated for high reflectivity (often called an FP etalon). If we assume  $L = 1$  cm and  $n_r = 1.54$ , the free spectral range for near-normal incidence, i.e., for  $\theta \cong 0$ , is  $\Delta v_{fsr} = c/2n_r L = 9.7$  GHz. If we now take  $R_1 = R_2 = 0.98$ , we obtain from Eq. (4.5.14a) a finesse  $F \cong 150$ , so that  $\Delta v_c = \Delta v_{fsr}/F = 65$  MHz. According to Eq. (4.5.9), for a lossless coating, the peak transmission is  $T_{max} = 1$ ; the minimum transmission, according to Eq. (4.5.10), is  $T_{min} \cong 10^{-4}$ . Note the very small value of  $T_{min}$ .

**Example 4.4.** *Spectral measurement of an  $Ar^+$ -laser output beam.* We consider an Ar-ion laser oscillating on its green line at a wavelength  $\lambda = 514.5$ -nm. We assume that the laser is oscillating on many longitudinal modes encompassing the full Doppler width of the laser line ( $\Delta v_0^* = 3.5$  GHz). Thus we have  $\Delta v_{osc} = \Delta v_0^* = 3.5$  GHz. To avoid frequency ambiguity, we must have  $\Delta v_{fsr} = (c/2L) \geq 3.5$  GHz i.e.,  $L \leq 4.28$  cm. If we now assume a finesse  $F = 150$  and take  $L = 4.28$  cm, according to Eq. (4.5.18) we have, for the interferometer resolution,  $\Delta v_m = \Delta v_{osc}/F \cong 23$  MHz. If, for example, the length of the laser cavity is  $L_1 = 1.5$  m, consecutive longitudinal modes are separated (see Chap. 5) by  $\Delta v = c/2L_1 = 100$  MHz. Since  $\Delta v_m < \Delta v$ , the FP interferometer is able to resolve these longitudinal modes. Note that, since the frequency of the laser light is  $\nu = c/\lambda \cong 5.83 \times 10^{14}$  Hz, the corresponding resolving power of the interferometer is  $\nu/\Delta v_m = 2.54 \times 10^7$ . This is a very high resolving power compared, e.g., to the best that can be obtained with a grating spectrometer ( $\nu/\Delta v_m < 10^6$ ).